Octal Bus Buffer

Inverting

The MC74VHCT540A is an advanced high speed CMOS inverting octal bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHCT540A features inputs and outputs on opposite sides of the package and two AND-ed active-low output enables. When either $\overline{\text{OE1}}$ or $\overline{\text{OE2}}$ are high, the terminal outputs are in the high impedance state.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The VHCT540A input and output (when disabled) structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 3.7 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4.0 \,\mu\text{A}$ (Max) at $T_A = 25^{\circ}\text{C}$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 1.2 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 124 FETs or 31 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant



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MARKING DIAGRAM



SOEIAJ-20 M SUFFIX CASE 967



A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

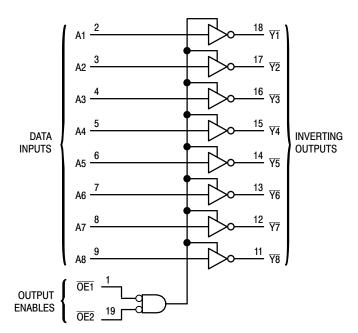
FUNCTION TABLE

	Inputs	Output V	
OE1	OE2	Α	Output ₹
L	L	L	Н
L	L	Н	L
H	Х	Х	Z
X	Н	Х	Z

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT540AMG	SOEIAJ	40 Units/Rail
MC74VHCT540AMELG	SOEIAJ	2000 Units/T&R

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.



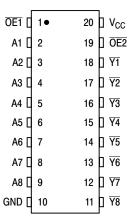


Figure 1. Logic Diagram

Figure 2. Pin Assignment

MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage	- 0.5 to + 7.0	V
V _{out}	DC Output Voltage	- 0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current	- 20	mA
I _{OK}	Output Diode Current	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 75	mA
P _D	Power Dissipation in Still Air (Note 2) SOIC Packages TSSOP Package	500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those
indicated may adversely affect device reliability. Functional operation under absolute maximum-rated conditions is not implied. Functional
operation should be restricted to the Recommended Operating Conditions.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	4.5	5.5	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage Outputs in 3-State High or Low State	0	5.5 V _{CC}	V
T _A	Operating Temperature	-55	125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 5.0 \text{ V } \pm 0.5 \text{ V}$	0	20	ns/V

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	7	Γ _A = 25°()	T _A ≤	85°C	T _A ≤ 125°C		
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		3.0 4.5 5.5	1.2 2.0 2.0			1.2 2.0 2.0		1.2 2.0 2.0		V
V _{IL}	Maximum Low-Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -50 \mu A$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	$V_{IN} = V_{IH}$ or V_{IL}	$\begin{aligned} V_{IN} &= V_{IH} \text{ or } V_{IL} \\ I_{OH} &= -4.0 \text{ mA} \\ I_{OH} &= -8.0 \text{ mA} \end{aligned}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 50 \mu A$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH}$ or V_{IL}	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OL} = 4.0 \text{ mA} \\ &I_{OL} = 8.0 \text{ mA} \end{aligned}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μА
Icc	Maximum Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	5.5			2.0		20		40	μА
I _{CCT}	Quiescent Supply Current	Input: V _{IN} = 3.4 V	5.5			1.35		1.50		1.65	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0.0			0.5		5.0		10	μΑ

operation should be restricted to the Recommended Operating Conditions.

2. Derating - SOIC Packages: - 7.0 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

			-	T _A = 25°C			- 40 to ⊳°C	T _A ≤ 1	125°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to ₹	$V_{CC} = 3.3 \pm 0.3 \text{ V C}_{L} = 15 \text{ pF}$ $C_{L} = 50 \text{ pF}$		4.8 7.3	7.0 10.5	1.0 1.0	8.5 12.0		10.5 14.0	ns
	(Figures 1 and 3)	$V_{CC} = 5.0 \pm 0.5 \text{ V C}_{L} = 15 \text{ pF}$ $C_{L} = 50 \text{ pF}$		3.7 5.2	5.0 7.0	1.0 1.0	6.0 8.0		8.0 10.0	
t _{PZL} , t _{PZH}	Output Enable Time, OEn to \(\text{V} \)	$V_{CC} = 3.3 \pm 0.3 \text{ V C}_{L} = 15 \text{ pF}$ $R_{L} = 1.0 \text{ k}\Omega$ $C_{L} = 50 \text{ pF}$		6.8 9.3	10.5 14.0	1.0 1.0	12.5 16.0		15.0 19.0	ns
	(Figures 2 and 4)	$\begin{aligned} &V_{CC} = 5.0 \pm 0.5 \text{ V C}_{L} = 15 \text{ pF} \\ &R_{L} = 1.0 \text{ k}\Omega \qquad &C_{L} = 50 \text{ pF} \end{aligned}$		4.7 6.2	7.2 9.2	1.0 1.0	8.5 10.5		10.5 13.0	
t _{PLZ} , t _{PHZ}	Output Disable Time, OEn to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V C}_{L} = 50 \text{ pF}$ $R_{L} = 1.0 \text{ k}\Omega$		11.2	15.4	1.0	17.5		20.0	ns
	(Figures 2 and 4)	$V_{CC} = 5.0 \pm 0.5 \text{ V C}_{L} = 50 \text{ pF}$ $R_{L} = 1.0 \text{ k}\Omega$		6.0	8.8	1.0	10.0		11.5	
t _{OSLH} , t _{OSHL}	Output to Output Skew	$V_{CC} = 3.3 \pm 0.3 \text{ V C}_{L} = 50 \text{ pF}$ (Note 3)			1.5		1.5		2.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V C}_{L} = 50 \text{ pF}$ (Note 3)			1.0		1.0		1.5	ns
C _{in}	Maximum Input Capacitance			4.0	10		10		10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High Impedance State)			6.0						pF

Ī			Typical @ 25°C, V _{CC} = 5.0V	
	C_{PD}	Power Dissipation Capacitance (Note 4)	17	pF

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		T _A = 25°C		
Symbol	Parameter	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.9	1.2	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	- 0.9	-1.2	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/8$ (per bit). C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

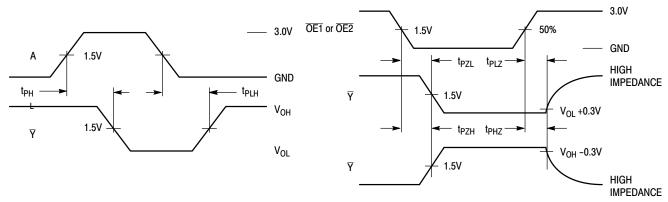
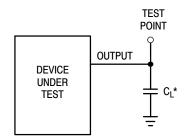


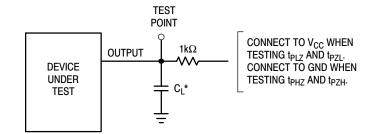
Figure 3. Switching Waveform

Figure 4. Switching Waveform



*Includes all probe and jig capacitance

Figure 5. Test Circuit

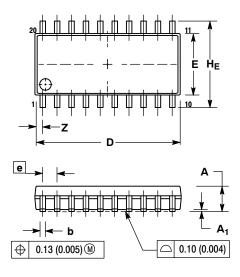


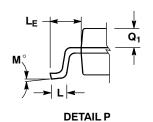
*Includes all probe and jig capacitance

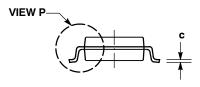
Figure 6. Test Circuit

PACKAGE DIMENSIONS

SOEIAJ-20 M SUFFIX CASE 967-01 ISSUE A







NOTES:

- DIMENSIONING AND TOLERANCING PER
 ANSLY 14 FM 1992
- ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLUDE
 MOLD FLASH OR PROTRUSIONS AND ARE
 MEASURED AT THE PARTING LINE. MOLD
 FLASH OR PROTRUSIONS SHALL NOT EXCEED
 0.15 (0.006) PER SIDE.

 TERMINAL NUMBERS ARE SHOWN FOR
- 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- HEFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

MILLIN	IETERS	INC	HES
MIN	MAX	MIN	MAX
	2.05		0.081
0.05	0.20	0.002	0.008
0.35	0.50	0.014	0.020
0.15	0.25	0.006	0.010
12.35	12.80	0.486	0.504
5.10	5.45	0.201	0.215
1.27	BSC	0.050	BSC
7.40	8.20	0.291	0.323
0.50	0.85	0.020	0.033
1.10	1.50	0.043	0.059
0 °	10 °	0 °	10°
0.70	0.90	0.028	0.035
	0.81		0.032
	MIN 0.05 0.35 0.15 12.35 5.10 1.27 7.40 0.50 1.10 0 °	2.05 0.05 0.20 0.35 0.50 0.15 0.25 12.35 12.80 5.10 5.45 1.27 BSC 7.40 8.20 0.50 0.85 1.10 1.50 0 ° 10 ° 0.90	MIN MAX MIN 2.05 0.05 0.20 0.002 0.35 0.50 0.014 0.15 0.25 0.006 12.35 12.80 0.486 5.10 5.45 0.201 1.27 BSC 0.050 7.40 8.20 0.291 0.50 0.85 0.020 1.10 1.50 0.043 0 ° 10 ° 0 ° 0.70 0.99 0.028

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